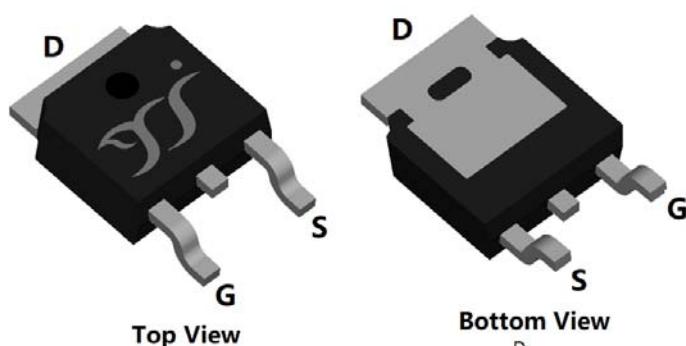
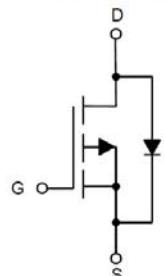


P-Channel Enhancement Mode Field Effect Transistor

**TO-252**

Product Summary

• V_{DS}	-100V
• I_D	-18A
• $R_{DS(on)}$ (at $V_{GS}=-10V$)	<110 mΩ
• $R_{DS(on)}$ (at $V_{GS}=-4.5V$)	<120 mΩ
• 100% EAS Tested	
• 100% ∇V_{DS} Tested	
• ESD Level(HBM)	Class 1B

General Description

- Split gate trench MOSFET technology
- Low $R_{DS(on)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Power management
- Portable equipment

■ Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	-100	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current	$T_c=25^\circ C$	I_D	-18	A
	$T_c=100^\circ C$		-12	
Pulsed Drain Current ^A		I_{DM}	-72	A
Avalanche energy ^B		EAS	72	mJ
Total Power Dissipation ^C	$T_c=25^\circ C$	P_D	72	W
	$T_c=100^\circ C$		29	
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+150	°C

■ Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient ^D	Steady-State	$R_{\theta JA}$	40	50	°C/W
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	1.35	1.7	

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJD18GP10A	F1/F2	YJD18GP10A	2500	/	25000	13" reel



YJD18GP10A

■ Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-100	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=-100\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-1	μA
		$V_{\text{DS}}=-100\text{V}, V_{\text{GS}}=0\text{V}, T_J=150^\circ\text{C}$	-	-	-100	
Gate-Body Leakage Current	I_{GSS}	$V_{\text{GS}}= \pm 20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 100	nA
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-1.0	-1.8	-2.5	V
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}}=-10\text{V}, I_{\text{D}}=-10\text{A}$	-	83	110	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-5\text{A}$	-	95	120	
Diode Forward Voltage	V_{SD}	$I_{\text{S}}=-10\text{A}, V_{\text{GS}}=0\text{V}$	-	-	-1.3	V
Gate resistance	R_{G}	$f=1\text{MHz}$	-	10	-	Ω
Maximum Body-Diode Continuous Current	I_{S}		-	-	-18	A
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{\text{DS}}=-50\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$	-	1051	-	pF
Output Capacitance	C_{oss}		-	119	-	
Reverse Transfer Capacitance	C_{rss}		-	25	-	
Switching Parameters						
Total Gate Charge	Q_{g}	$V_{\text{GS}}=-10\text{V}, V_{\text{DS}}=-50\text{V}, I_{\text{D}}=-5\text{A}$	-	20.1	-	nC
Gate-Source Charge	Q_{gs}		-	3.9	-	
Gate-Drain Charge	Q_{gd}		-	4.3	-	
Reverse Recovery Charge	Q_{rr}	$I_{\text{F}}=-5\text{A}, \text{di/dt}=100\text{A/us}$	-	140	-	nC
Reverse Recovery Time	t_{rr}		-	70	-	ns
Turn-on Delay Time	$t_{\text{D(on)}}$	$V_{\text{GS}}=-10\text{V}, V_{\text{DD}}=-50\text{V}, R_{\text{L}}=2.5\Omega, R_{\text{GEN}}=6\Omega$	-	10	-	ns
Turn-on Rise Time	t_{r}		-	30	-	
Turn-off Delay Time	$t_{\text{D(off)}}$		-	77	-	
Turn-off fall Time	t_{f}		-	81	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B. $T_J=25^\circ\text{C}, V_{\text{DD}}=-50\text{V}, V_{\text{G}}=-10\text{V}, R_{\text{G}}=25\Omega, L=0.5\text{mH}, I_{\text{AS}}=-17\text{A}$.

C. P_d is based on max. junction temperature, using junction-case thermal resistance.

D. The value of $R_{\theta_{JA}}$ is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design.



■ Typical Electrical and Thermal Characteristics Diagrams

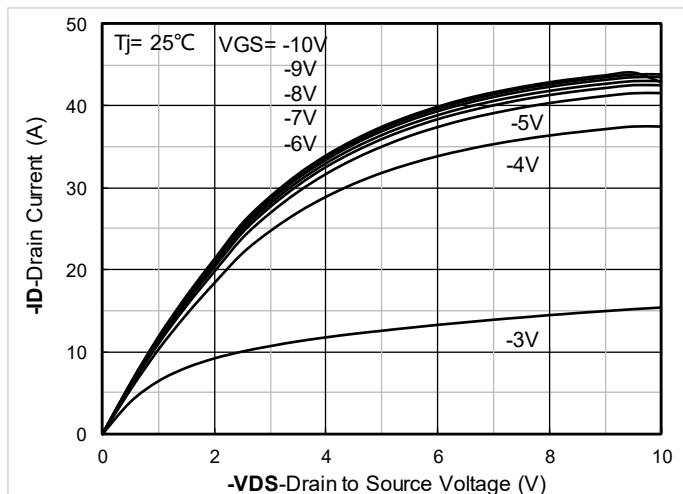


Figure 1. Output Characteristics

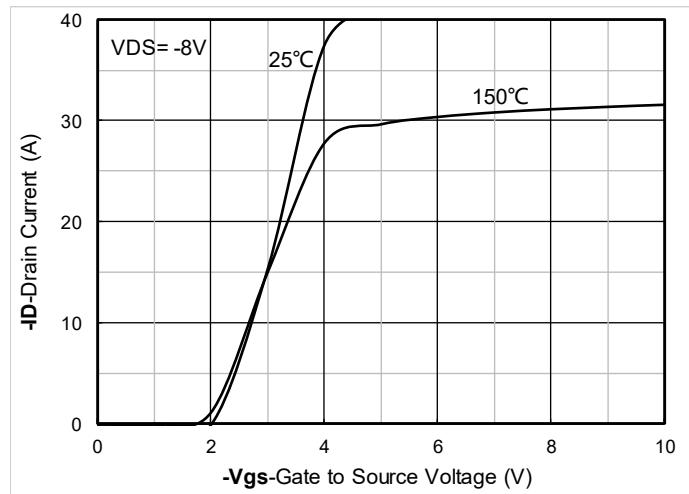


Figure 2. Transfer Characteristics

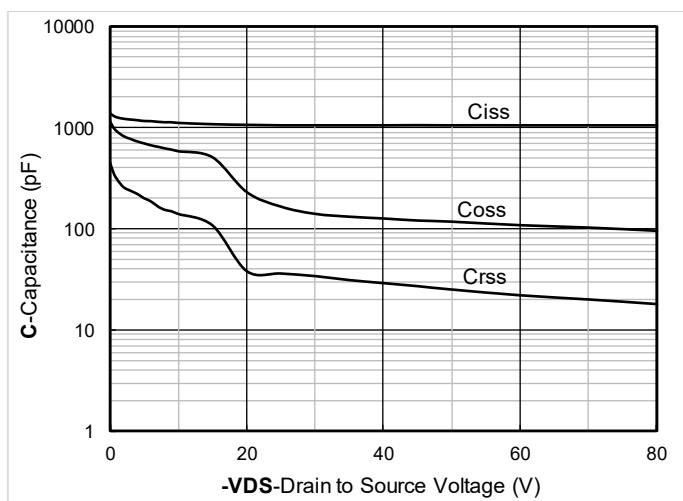


Figure 3. Capacitance Characteristics

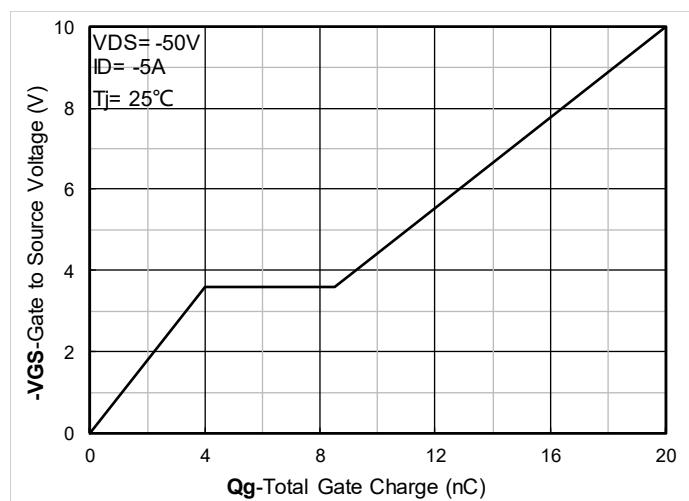


Figure 4. Gate Charge

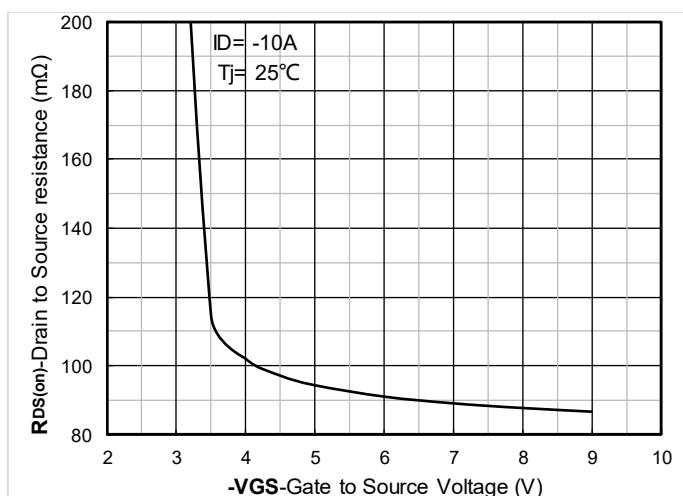


Figure 5. On-Resistance vs Gate to Source Voltage

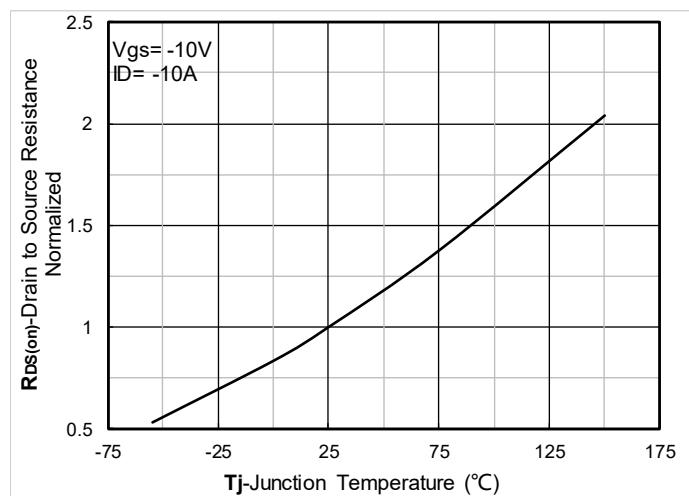


Figure 6. Normalized On-Resistance

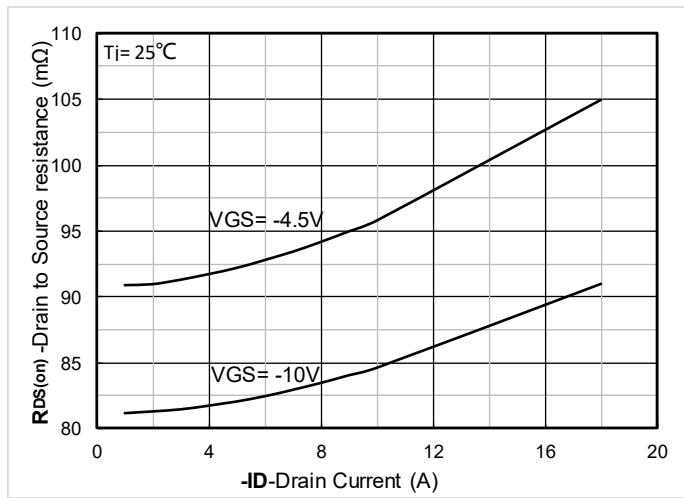


Figure7. RDS(on) VS Drain Current

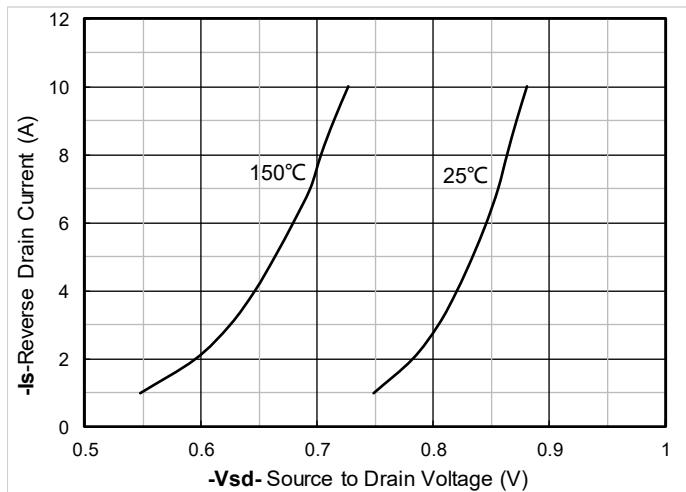


Figure8. Forward characteristics of reverse diode

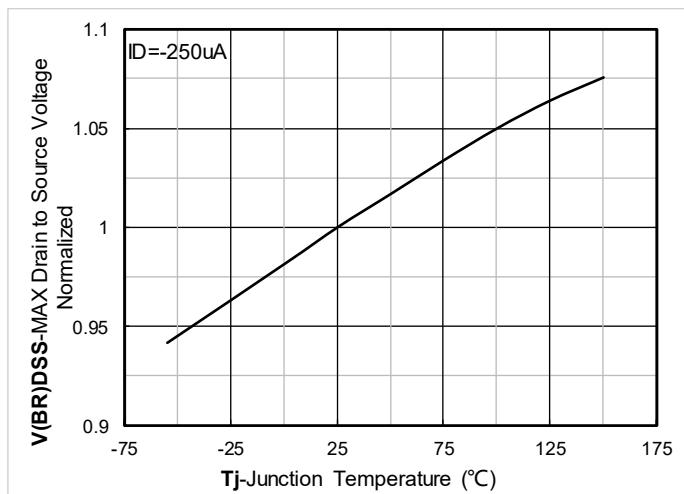


Figure9. Normalized breakdown voltage

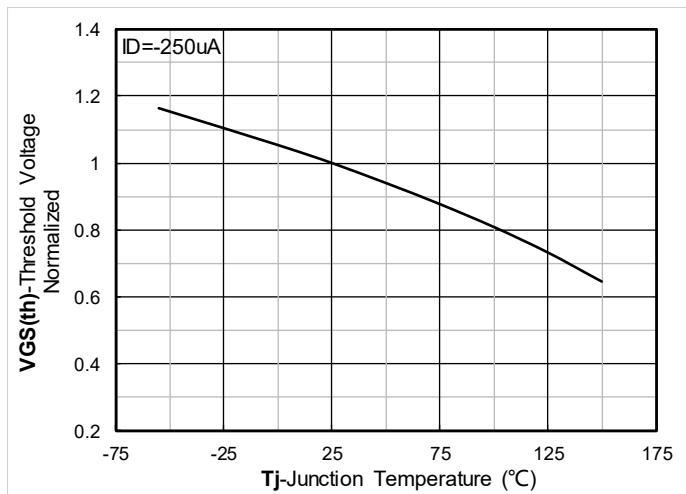


Figure10. Normalized Threshold voltage

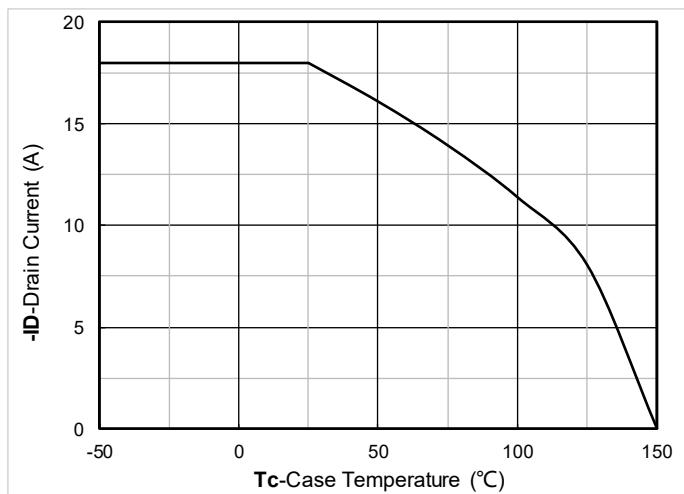


Figure11. Current dissipation

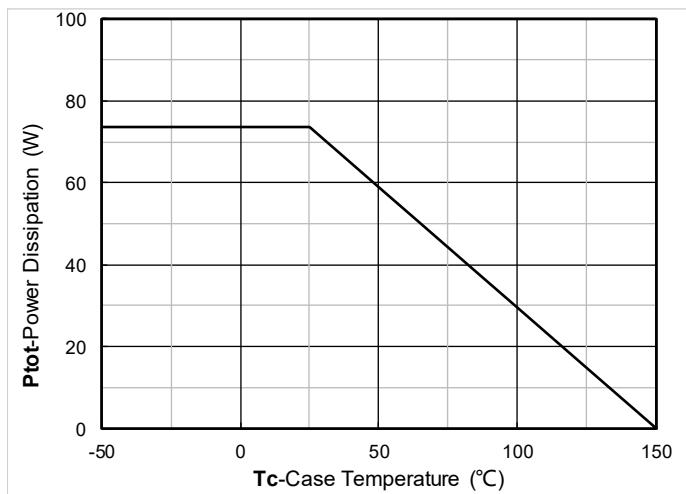


Figure12. Power dissipation

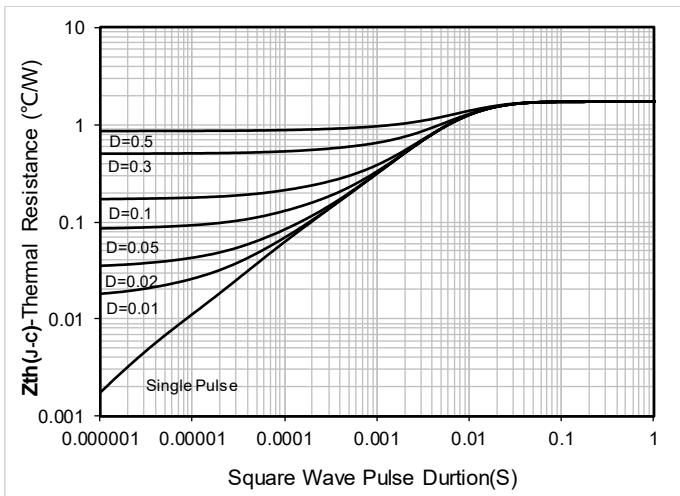


Figure13. Maximum Transient Thermal Impedance

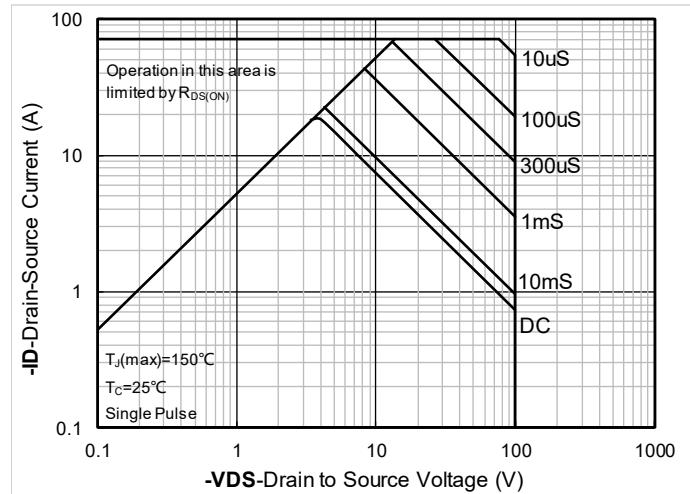
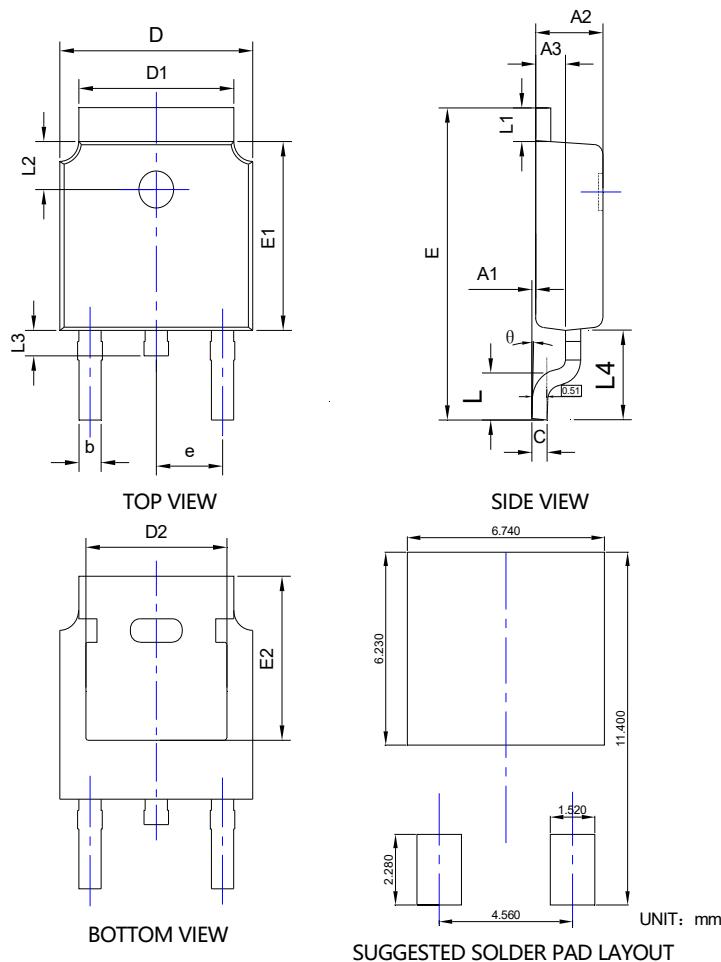


Figure14. Safe Operation Area



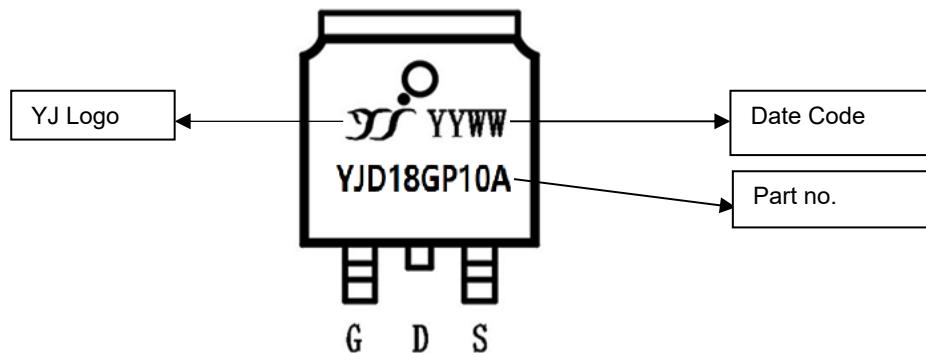
■ TO-252-B Package Information



SYMBOL	DIMENSIONS					
	INCHES			Millimeter		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A1	0.000	--	0.008	0.000	--	0.200
A2	0.087	0.091	0.094	2.200	2.300	2.400
A3	0.035	0.039	0.043	0.900	1.000	1.100
b	0.026	0.030	0.034	0.660	0.760	0.860
c	0.018	0.020	0.023	0.460	0.520	0.580
D	0.256	0.260	0.264	6.500	6.600	6.700
D1	0.203	0.209	0.215	5.150	5.300	5.450
D2	0.181	0.189	0.195	4.600	4.800	4.950
E	0.390	0.398	0.406	9.900	10.100	10.300
E1	0.236	0.240	0.244	6.000	6.100	6.200
E2	0.203	0.209	0.215	5.150	5.300	5.450
e	0.090BSC			2.286BSC		
L	0.049	0.059	0.069	1.250	1.500	1.750
L1	0.035	--	0.050	0.900	--	1.270
L2	0.055	--	0.075	1.400	--	1.900
L3	0.024	0.031	0.039	0.600	0.800	1.000
L4	0.114REF			2.900REF		
θ	0°	--	10°	0°	--	10°

NOTE:

1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
2. TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
3. THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.

**■ Marking Information****Note:**

1. All marking is at middle of the product body
2. All marking is in laser printing
3. YJD18GP10A is part no., YYWW is date code, "YY" is year, "WW" is week
4. Body color: Black



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The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use or sale.

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